



$V_R = 650\text{ V}$   
 $I_F = 6\text{ A (}T_C=148^\circ\text{C)}$   
 $Q_C = 15\text{ nC (}V_R=400\text{V)}$

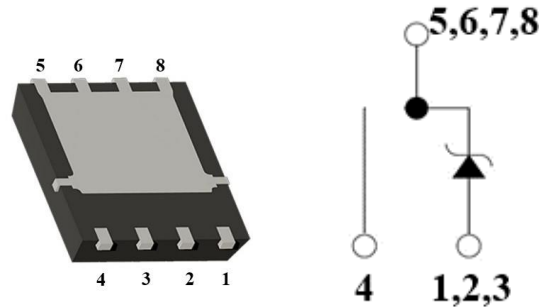
## Features

- Zero Forward/Reverse Recovery Current
- High Blocking Voltage
- High Frequency Operation
- Positive Temperature Coefficient on  $V_F$
- Temperature Independent Switching Behavior
- High surge current capability

## Benefits

- Higher System Efficiency
- Parallel Device Convenience without thermal runaway
- Higher Temperature Application
- No Switching loss
- Hard Switching & Higher Reliability
- Environmental Protection

DFN 5x6



## Applications

- PC Power
- Server Power Supply
- PFC Boost Topology
- AC/DC converters
- DC/DC converters
- Uninterruptable power supplies

## Maximum Ratings ( $T_C=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Value	Unit
Peak Repetitive Reverse Voltage	$V_{RRM}$		650	V
Peak Reverse Surge Voltage	$V_{RSM}$		650	V
DC Blocking Voltage	$V_R$		650	V
Continuous Forward Current	$I_F$	$T_C=25^\circ\text{C}$ $T_C=135^\circ\text{C}$ $T_C=148^\circ\text{C}$	16 7.5 6	A
Non repetitive Forward Surge Current	$I_{FSM}$	$T_C = 25^\circ\text{C}$ , $t_p=10\text{ ms}$ , Half Sine Pulse $T_C = 110^\circ\text{C}$ , $t_p=10\text{ ms}$ , Half Sine Pulse $T_C = 25^\circ\text{C}$ , $t_p=10\ \mu\text{s}$ , Square	33 25 200	A
Repetitive peak Forward Surge Current	$I_{FRM}$	$T_C = 25^\circ\text{C}$ , $t_p=10\text{ ms}$ , Freq = 0.1Hz, 100 cycles, Half Sine Pulse $T_C = 110^\circ\text{C}$ , $t_p=10\text{ ms}$ , Freq = 0.1Hz, 100 cycles, Half Sine Pulse	25 20	A
Total power dissipation	$P_D$	$T_C=25^\circ\text{C}$	60	W
Operating Junction Temperature	$T_J$		-55 to 175	$^\circ\text{C}$
Storage Temperature	$T_{STG}$		-55 to 175	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



### Electrical Characteristics

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
DC Blocking Voltage	$V_{DC}$	$I_R = 250\mu A, T_J = 25^\circ C$	650			V
Forward Voltage	$V_F$	$I_F = 6A, T_J = 25^\circ C$		1.45	1.8	V
		$I_F = 6A, T_J = 125^\circ C$		1.6		
		$I_F = 6A, T_J = 175^\circ C$		1.75		V
Reverse Current	$I_R$	$V_R = 650V, T_J = 25^\circ C$		5	80	$\mu A$
		$V_R = 650V, T_J = 125^\circ C$		25		$\mu A$
		$V_R = 650V, T_J = 175^\circ C$		60		$\mu A$
Total Capacitive Charge	$Q_C$	$V_R = 400V$ $T_J = 25^\circ C$		15		nC
Total Capacitance	C	$V_R = 1V, T_J = 25^\circ C,$ Freq = 1MHz		240		pF
		$V_R = 200V, T_J = 25^\circ C,$ Freq = 1MHz		30		
		$V_R = 400V, T_J = 25^\circ C,$ Freq = 1MHz		22		

Note: This is a majority carrier diode, so there is no reverse recovery charge

### Thermal Characteristics

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Thermal Resistance	$R_{th(j-c)}$	junction-case		2.5		$^\circ C/W$



### Typical Electrical Curves

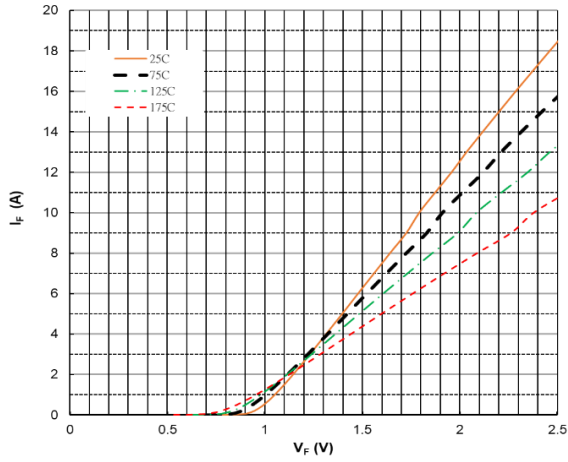


Figure 1. Forward Characteristics

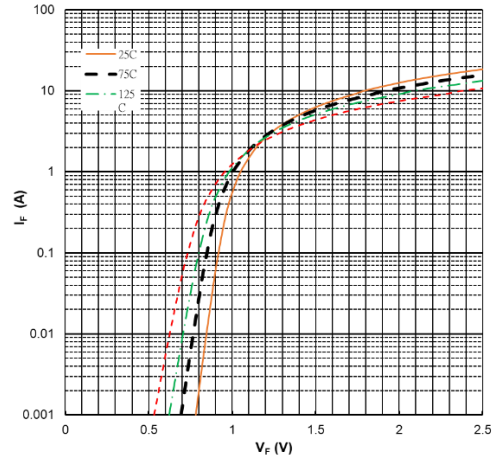


Figure 2. Forward Characteristics

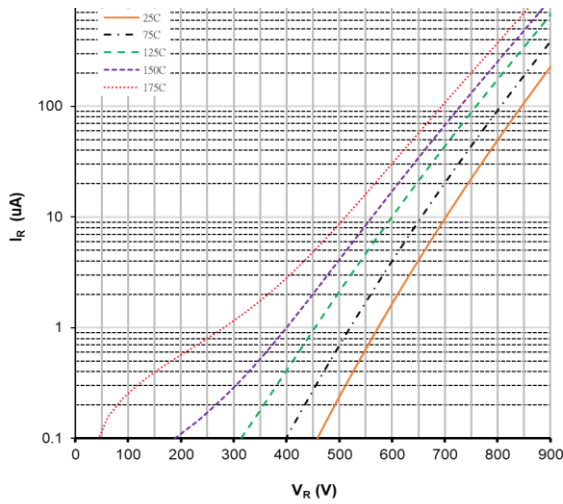


Figure 3. Reverse Characteristics

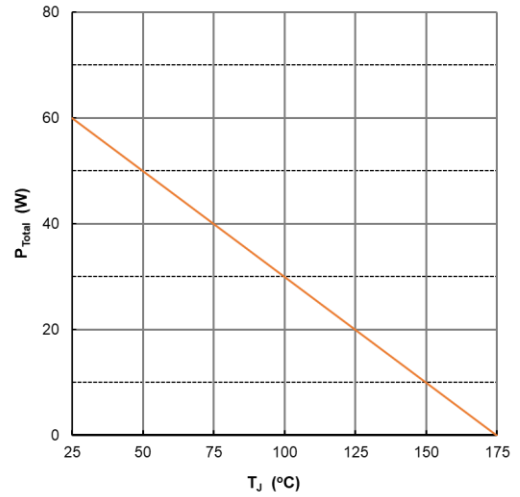


Figure 4. Power Derating

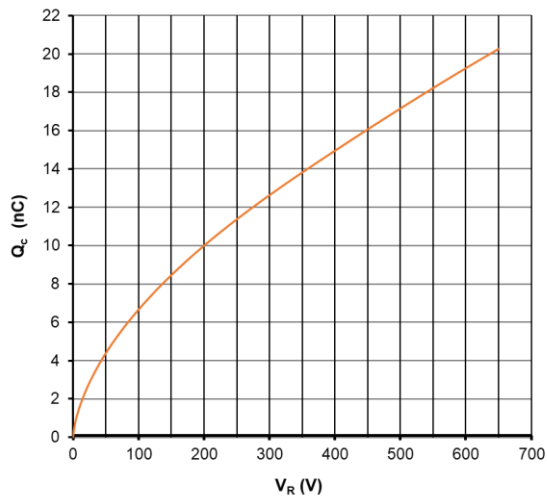


Figure 5. Reverse charge vs. Reverse Voltage

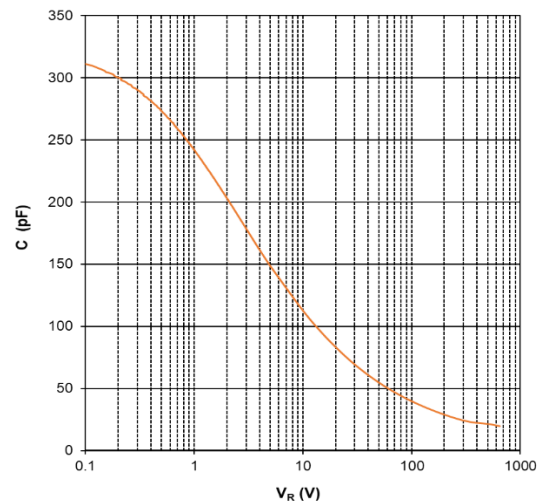
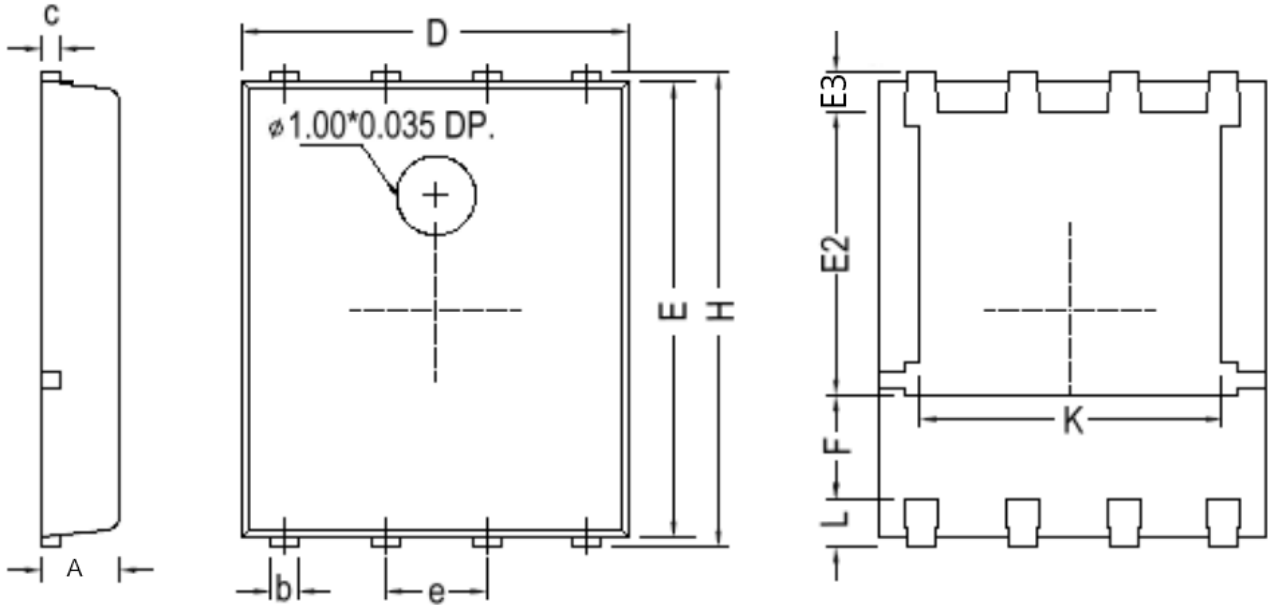


Figure 6. Capacitance vs. Reverse Voltage



## Package Dimensions

(DFN 5x6 Package)



Items	Millimeters		
	Min.	Nom.	Max.
A	1.0	1.1	1.2
b	0.3	0.4	0.5
c	0.244	0.254	0.264
D	5.0	5.2	5.4
E	5.66	5.86	6.06
E2	3.52	3.72	3.92
E3	0.4	0.5	0.6
e	1.17	1.27	1.37
F	1.15	1.3	1.45
H	5.95	6.15	6.35
L	0.3	0.6	0.7
K	3.8	4.1	4.25

## Ordering Information

Part Number	Package	Packing	Marking	Base Quantity
LGE3D06065N	DFN 5x6	3000pcs/Tape & Reel	LGE3D06065N	3000 PCS